

November 2013

# FDP18N50 / FDPF18N50 / FDPF18N50T N-Channel UniFET<sup>TM</sup> MOSFET 500 V, 18 A, 265 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 220  $m\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 9 A
- Low Gate Charge (Typ. 45 nC)
- Low C<sub>rss</sub> (Typ. 25 pF)
- · 100% Avalanche Tested

## **Applications**

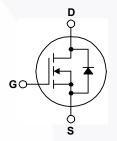
- LCD/LED/PDP TV
- Lighting
- · Uninterruptible Power Supply

# **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FDP18N50	FDPF18N50 / FDPF18N50T	Unit
$V_{DSS}$	Drain-Source Voltage		500		V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	18 10.8	18 * 10.8 *	A A
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	72	72 *	Α
V <sub>GSS</sub>	Gate-Source voltage		±30		V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		945		mJ
I <sub>AR</sub>	Avalanche Current (Note 1)		18		Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		23.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate Above 25°C	235 1.88	38.5 0.3	W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150		°C
T <sub>L</sub>	Maximum Lead Temperature 1/8" from Case for 5 Seconds	<u> </u>	300		°C

<sup>\*</sup> Drain current limited by maximum junction temperature

#### **Thermal Characteristics**

Symbol	Parameter	FDP18N50	8N50 FDPF18N50 / FDPF18N50T	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.53	3.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP18N50	FDP18N50	TO-220	Tube	N/A	N/A	50 units
FDPF18N50	FDPF18N50	TO-220F	Tube	N/A	N/A	50 units
FDPF18N50T	FDPF18N50T	TO-220F	Tube	N/A	N/A	50 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	500			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics			1		
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9 A		0.220	0.265	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 9 A		25		S
Dynamic C	Characteristics			1		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,		2200	2860	pF
C <sub>oss</sub>	Output Capacitance	f = 1 MHz		330	430	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			25	40	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 18 A,		55	120	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_G = 25 \Omega$		165	340	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			95	200	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	90	190	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 18 A,		45	60	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		12.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		19		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
Is	Maximum Continuous Drain-Source Diode Forward Current				18	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				72	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 18 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 18 A,		500		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt =100 A/μs		5.4		μС

#### Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 5.2 mH, I<sub>AS</sub> = 18 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.
- 3.  $I_{SD} \le$  18 A, di/dt  $\le$  200 A/ $\mu$ s,  $V_{DD} \le$  BV $_{DSS}$ , starting  $T_J$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

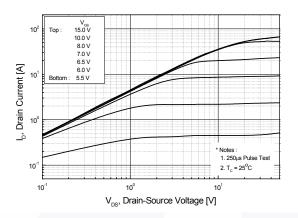


Figure 2. Transfer Characteristics

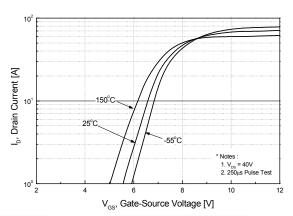
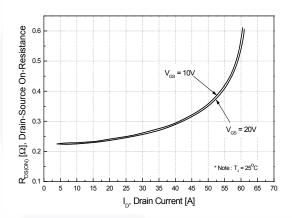


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



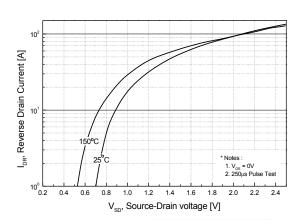


Figure 5. Capacitance Characteristics

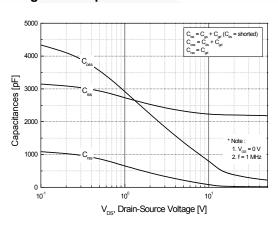
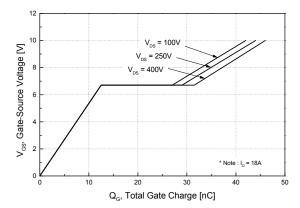


Figure 6. Gate Charge Characteristics



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

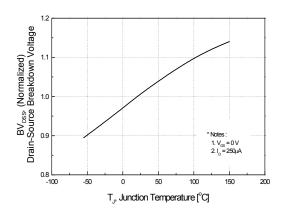


Figure 8. On-Resistance Variation vs. Temperature

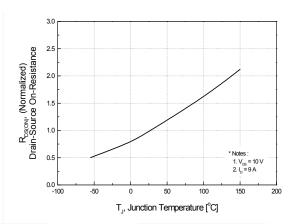
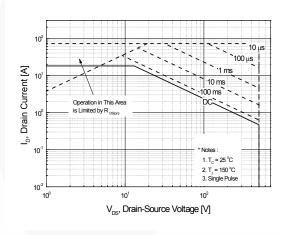


Figure 9-1. Maximum Safe Operating Area - FDP18N50





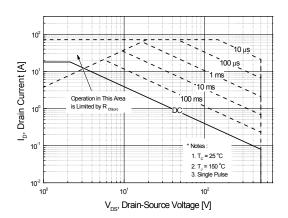
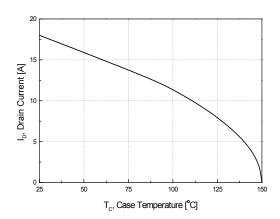


Figure 10. Maximum Drain Current vs. Case Temperature



# **Typical Performance Characteristics** (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP18N50

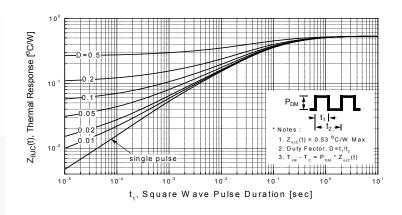
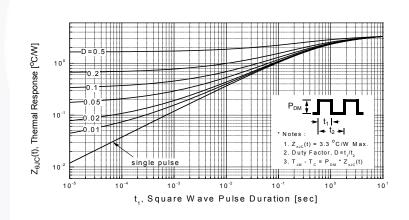


Figure 11-2. Transient Thermal Response Curve - FDPF18N50 / FDPF18N50T



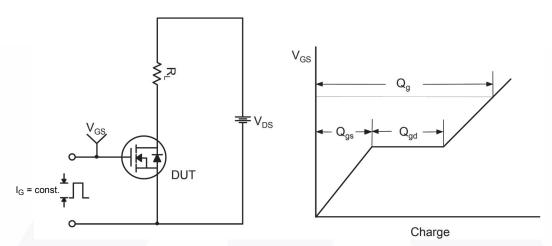


Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms

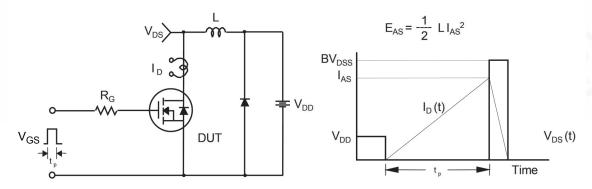


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

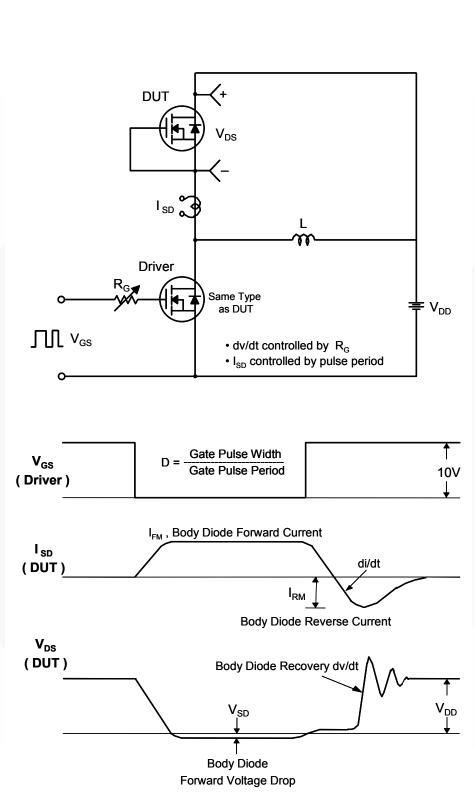


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

### **Mechanical Dimensions**

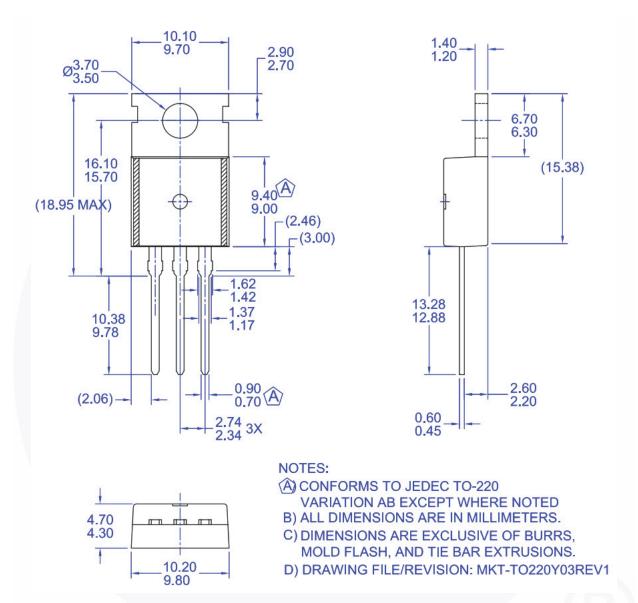


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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### **Mechanical Dimensions**

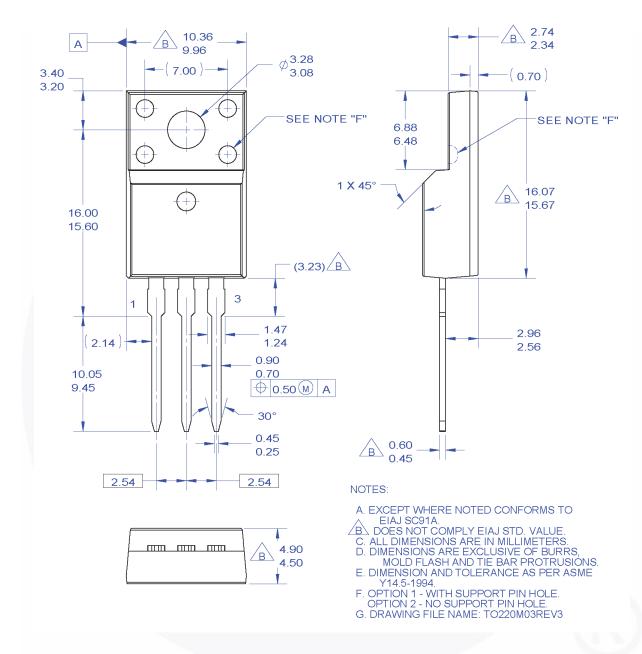


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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